

# 2SD2620G

## Silicon NPN epitaxial planar type

For low-frequency driver amplification

### ■ Features

- High forward current transfer ratio  $h_{FE}$
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- High emitter-base voltage (Collector open)  $V_{EBO}$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	100	V
Collector-emitter voltage (Base open)	$V_{CEO}$	100	V
Emitter-base voltage (Collector open)	$V_{EBO}$	15	V
Collector current	$I_C$	20	mA
Peak collector current	$I_{CP}$	50	mA
Collector power dissipation	$P_C$	125	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

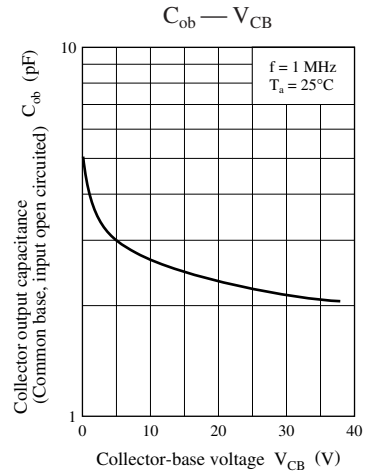
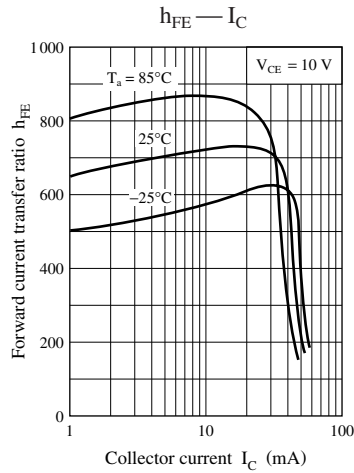
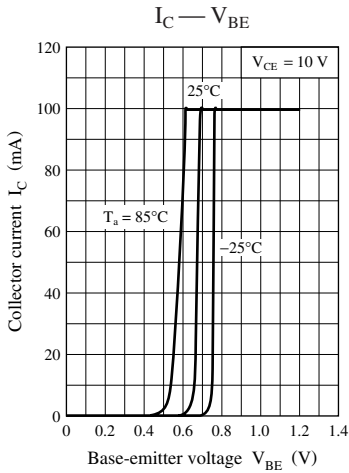
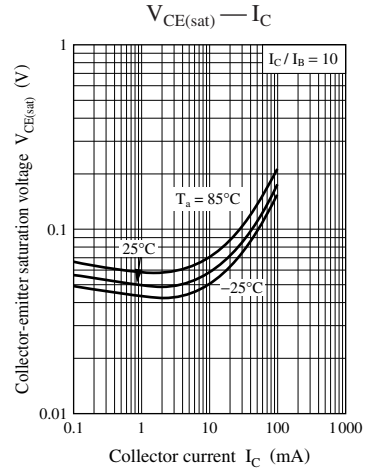
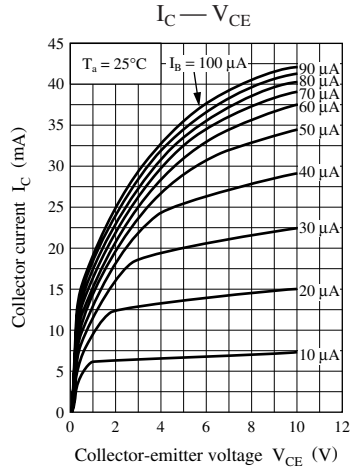
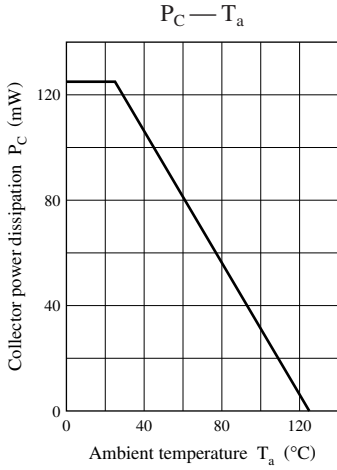
### ■ Package

- Code  
SSMini3-F3
- Marking Symbol: 3B
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

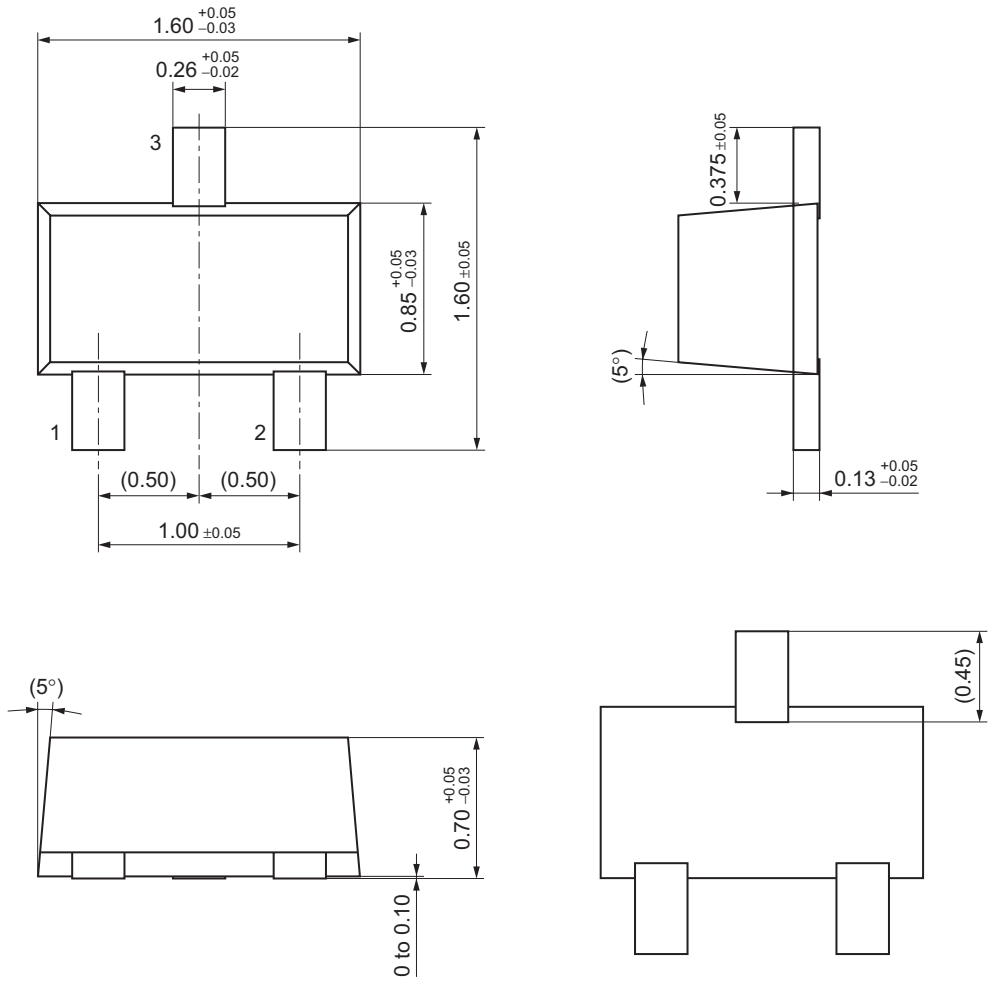
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}$ , $I_E = 0$	100			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 1 \text{ mA}$ , $I_B = 0$	100			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10 \mu\text{A}$ , $I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 60 \text{ V}$ , $I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 60 \text{ V}$ , $I_B = 0$			1.0	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 2 \text{ mA}$	400		1200	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}$ , $I_B = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}$ , $I_E = -2 \text{ mA}$ , $f = 200 \text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CE} = 10 \text{ V}$ , $I_C = 1 \text{ mA}$ , $G_V = 80 \text{ dB}$ $R_g = 100 \text{ k}\Omega$ , Function = FLAT		80		mV

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



SSMini3-F3

Unit: mm



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